
APPENDIX VI

STATUTORY AND GENERAL INFORMATION

A. FURTHER INFORMATION ABOUT OUR GROUP

1. Incorporation of Our Company

Our Company was established as a limited liability company under the laws of the PRC on 18 April 2014, and was converted into a joint stock company with limited liability on 8 February 2021. We were registered with the Registrar of Companies in Hong Kong as a non-Hong Kong company under Part 16 of the Companies Ordinance on 6 January 2026, and have established a place of business in Hong Kong at Unit 512 of the 5th Floor of Building 12W, Phase Three, Hong Kong Science Park, Pak Shek Kok, New Territories, Hong Kong. Ms. Huang Shiyao (黃詩瑤) has been appointed as the authorized representative of our Company for the acceptance of service of process and notices in Hong Kong. The address for service of process on our Company in Hong Kong is the same as our principal place of business in Hong Kong as set out above.

As our Company is incorporated in the PRC, our operations are subject to the relevant laws and regulations of the PRC. A summary of our Articles of Association and relevant aspects of PRC law is set out in “Taxation and Foreign Exchange,” “Summary of Principal Legal and Regulatory Provisions” and “Summary of the Articles of Association” in Appendices III, IV and V to this document, respectively.

2. Changes in the Share Capital of Our Company

Our registered capital as at the date of our incorporation was RMB8,000,000, which has been fully paid up. On 8 February 2021, our Company was converted into a joint stock limited company with the shares capital of RMB10,300,000 divided into 10,300,000 Shares with a nominal value of RMB1.00 each.

Save as disclosed above in this appendix, there has been no alteration in the share capital of our Company within the two years immediately preceding the date of this document.

Immediately following the completion of the [REDACTED] and the conversion of Domestic Unlisted Shares into H Shares, assuming the [REDACTED] is not exercised, the share capital of our Company will be RMB[REDACTED] divided into [REDACTED] H Shares.

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3. The extraordinary general meeting of our Company held on 4 January 2026

Pursuant to the extraordinary general meeting of our Company held on 4 January 2026, the following resolutions, among other resolutions, were duly passed:

- (a) the issue of H Shares representing up to 25% of the total share capital of our Company upon completion of the [REDACTED] (before the exercise of the [REDACTED]) and such H Shares to be [REDACTED] on the Stock Exchange;
- (b) the granting of the [REDACTED] in respect of no more than 15% of the number of H Shares initially issued pursuant to the [REDACTED];
- (c) subject to the completion of the filing with the CSRC, upon completion of the [REDACTED], 103,000,000 Domestic Unlisted Shares held by certain existing Shareholders will be converted into H Shares on a one-for-one basis;
- (d) subject to the completion of the [REDACTED], the Articles of Association have been approved and adopted which will become effective from the [REDACTED], and our Board and person(s) authorized by our Board have been authorized to amend the Articles of Association in accordance with any comments from the Stock Exchange and the relevant PRC regulatory authorities; and
- (e) approving the Board and person(s) authorized by the Board to handle all matters relating to, among other things, the issue and the [REDACTED] of H Shares on the Stock Exchange.

4. Conversion into a joint stock company

Our Company was converted into a joint stock company with limited liability under the PRC Company Law in preparation of our [REDACTED]. For details, please see “History, Development and Corporate Structure — Corporate Development — 13. Conversion into a joint stock company” in this document. As confirmed by our PRC Legal Advisors, such conversion and all the equity transfers and capital increases as described in the section headed “History, Development and Corporate Structure” have obtained all necessary approvals from competent authorities or made all necessary registration or filings with the relevant authorities.

5. Changes in the Share Capital of Our Subsidiaries

A summary of the corporate information and the particulars of our subsidiaries are set out in Note 35 to the Accountants’ Report in Appendix I to this document.

The following subsidiaries of our Company were incorporated within two years immediately preceding the date of this document:

Name of subsidiary	Place of incorporation	Date of incorporation	Initial registered capital/share capital
Shenzhen PleiAI	PRC	11 December 2025	RMB1,000,000

There has been no alteration in the share capital of any of our subsidiaries within the two years immediately preceding the date of this Document.

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B. FURTHER INFORMATION ABOUT OUR BUSINESS

1. Summary of Material Contracts

The following contract (not being contracts entered into in the ordinary course of the business carried on or intended to be carried on by our Company) was entered into by the members of our Group within the two years preceding the date of this document, and is or may be material:

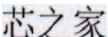
(a) the Deed of Non-Competition; and

(b) the [REDACTED].

2. Our Intellectual Property Rights

(a) Trademarks

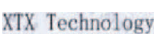
As of the Latest Practicable Date, we had registered the following trademarks which we consider to be material in relation to our business:

No.	Trademark	Class	Registrant	Place of registration	Registration number	Registration Date	Expiry date
1.		9, 42	Hong Kong XTX	Hong Kong	303771108AA	11 May 2016	10 May 2036
2.		9, 42	Hong Kong XTX	Hong Kong	303771108AB	11 May 2016	10 May 2036
3.		9	Our Company	Taiwan	1931785	16 August 2018	15 August 2028
4.		9	Our Company	Japan	2017-158580 6075840	31 August 2018	30 August 2028
5.		9	Our Company	South Korea	4020170153060 40-1437633	16 January 2019	15 January 2029
6.		9	Our Company	PRC	22465033	21 April 2019	20 April 2029
7.		9	Our Company	PRC	41615075	21 June 2020	20 June 2030
8.		9	Our Company	PRC	41615085	21 June 2020	20 June 2030
9.		42	Our Company	PRC	41613516	21 June 2020	20 June 2030
10.		42	Our Company	PRC	41620023	21 June 2020	20 June 2030
11.		9	Our Company	Russia	1554098	23 June 2020	22 June 2030
12.		9	Our Company	Philippines	M11554098	23 June 2020	22 June 2030
13.		9	Our Company	India	4702550 1554098	23 June 2020	22 June 2030
14.		9	Our Company	the United Kingdom	W00000001554098 1554098	23 June 2020	22 June 2030
15.		9	Our Company	European Union	1554098	23 June 2020	22 June 2030

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No.	Trademark	Class	Registrant	Place of registration	Registration number	Registration Date	Expiry date
16.		9	Our Company	Indonesia	M0020201554098	23 June 2020	22 June 2030
17.		9	Our Company	Vietnam	1554098	23 June 2020	22 June 2030
18.		9	Our Company	Brazil	501554098	23 June 2020	22 June 2030
19.		9	Our Company	Mexico	2436011 2327936 1554098	23 June 2020	22 June 2030
20.		9	Our Company	Malaysia	TM2020023273 1554098	23 June 2020	22 June 2030
21.		9	Our Company	Cambodia	KH/1554098/M KH/M/1554098 1554098	23 June 2020	22 June 2030
22.		9	Our Company	Canada	2056206 TMA1129988 1554098	23 June 2020	22 June 2030
23.		9	Our Company	Brunei	1554098/M 1554098	23 June 2020	22 June 2030
24.		9	Our Company	Laos	1554098 M/1554098 52135	23 June 2020	22 June 2030
25.		9	Our Company	Singapore	1554098 40202021193T	23 June 2020	22 June 2030
26.		9	Our Company	Thailand	1554098 200139442 251100192	23 June 2020	22 June 2030
27.		42	Our Company	PRC	42941968	28 April 2021	27 April 2031
28.		9	Our Company	PRC	42363518	21 August 2021	20 August 2031
29.		9	Our Company	PRC	42368373	21 August 2021	20 August 2031
30.		35	Our Company	PRC	42952803	21 August 2021	20 August 2031
31.		9	Our Company	PRC	46905664	21 December 2021	20 December 2031
32.		9	Our Company	PRC	47745649	7 January 2022	6 January 2032
33.		42	Our Company	PRC	61014482	14 May 2022	13 May 2032
34.		9	Our Company	PRC	61004938	21 May 2022	20 May 2032
35.		42	Our Company	PRC	61024023	7 June 2022	6 June 2032
36.		9	Our Company	PRC	61033077	28 July 2022	27 July 2032
37.		42	Our Company	PRC	61049029	14 August 2022	13 August 2032

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No.	Trademark	Class	Registrant	Place of registration	Registration number	Registration Date	Expiry date
38.		9	Our Company	PRC	61006448	14 August 2022	13 August 2032
39.		9	Our Company	United States	97634694 7319540	5 March 2024	4 March 2034
40.		9	Shenzhen Linkon Micro	PRC	74527528	7 April 2024	6 April 2034
41.		9	Shenzhen Bohr Micro	PRC	74516834	21 June 2024	20 June 2034
42.		9	Shenzhen Bohr Micro	PRC	74534704	21 June 2024	20 June 2034
43.		9	Our Company	PRC	78805034	28 November 2024	27 November 2034
44.		9, 42	Our Company	PRC	78824032	7 December 2024	6 December 2034
45.		9, 42	Our Company	PRC	78825792	7 December 2024	6 December 2034
46.		9	Shenzhen Bohr Micro	PRC	76960742	14 December 2024	13 December 2034
47.		9	Our Company	PRC	79825189	28 January 2025	27 January 2035
48.		9	Our Company	PRC	78811033	7 February 2025	6 February 2035
49.		9	Shenzhen Bohr Micro	PRC	79323858	7 February 2025	6 February 2035
50.		9	Shenzhen Bohr Micro	PRC	79310267	14 February 2025	13 February 2035
51.		9	Hong Kong XTX	Hong Kong	307000235	19 August 2025	18 August 2035

(b) Patents

As of the Latest Practicable Date, we had registered the following patents which we consider to be material to our business:

No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
1.	LGA8-packaged small-capacity SD memory card (基於LGA8封裝的小容量SD儲存卡)	Utility Model	Our Company	PRC	ZL201820050193.5	24 July 2018	10 January 2028
2.	A pin configuration structure for a Nand flash BGA package (一種Nand閃存球陣列封裝的管腳排布結構).	Utility Model	Our Company	PRC	ZL201821549872.3	26 April 2019	20 September 2028
3.	A packaging structure for a dual SLC flash memory chip (一種雙SLC閃存晶片的封裝結構).	Utility Model	Our Company	PRC	ZL201821549544.3	26 April 2019	20 September 2028

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
4.	Nor flash DFN package structure (Nor閃存DFN封裝結構).	Utility Model	Our Company	PRC	ZL201920878219.X	20 December 2019	11 June 2029
5.	A system for testing a response protected monotonic counter (RPMC) (對應答保護單調計數器RPMC進行測試的系統). .	Inventory Patent	Our Company	PRC	ZL202010226475.8	24 July 2020	26 March 2040
6.	A power-on reset circuit for stable power-on reset voltage (一種上電複位電壓穩定的上電複位電路).	Inventory Patent	Our Company	PRC	ZL201910062248.3	28 July 2020	22 January 2039
7.	A method and system for modeling a NAND flash memory storage cell (一種NAND閃存存儲單元的建模方法及系統).	Inventory Patent	Our Company	PRC	ZL201910509855.X	4 August 2020	12 June 2039
8.	Response protected monotonic counter and method for managing its count value (應答保護單調計數器及管理其計數值的方法).	Inventory Patent	Our Company	PRC	ZL202010366817.6	7 August 2020	29 April 2040
9.	A bandgap reference voltage high-speed power-on anti-overshoot circuit (一種帶隙基準電壓高速上電防過沖電路). . .	Inventory Patent	Our Company	PRC	ZL201910167082.1	14 August 2020	5 March 2039
10.	A method for simultaneously testing multiple Nor Flash samples (多顆Nor Flash樣品同時測試的方法).	Inventory Patent	Our Company	PRC	ZL202010345037.3	21 August 2020	26 April 2040
11.	A method for erasing Nor Flash (一種Nor Flash的擦除方法).	Inventory Patent	Our Company	PRC	ZL202010363840.X	1 September 2020	29 April 2040
12.	Method, system, storage medium, and terminal for reducing NAND flash read operation pump area (減少非型閃存讀操作泵面積方法、系統、儲存介質和終端).	Inventory Patent	Our Company	PRC	ZL202010490112.5	4 September 2020	1 June 2040
13.	A multi-die stacked memory and method for output synchronization thereof (一種多晶元疊封存儲器及其輸出同步方法). .	Inventory Patent	Our Company	PRC	ZL201911389198.6	15 September 2020	29 December 2039
14.	A power-down detection circuit (一種掉電檢測電路).	Inventory Patent	Our Company	PRC	ZL201911389778.5	22 September 2020	29 December 2039
15.	A flash memory (一種快閃存儲器). . . .	Inventory Patent	Our Company	PRC	ZL201911387774.3	29 September 2020	29 December 2039
16.	A new type of power-on power-off reset circuit (一種新型的上電下電複位電路). .	Inventory Patent	Our Company	PRC	ZL202010581454.8	29 September 2020	22 June 2040

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
17.	Nor Flash chip and a method for eliminating over-erasure during its erasure process (Nor Flash芯片及其擦除過程中消除過擦除的方法)	Inventory Patent	Our Company	PRC	ZL202010291263.8	2 October 2020	13 April 2040
18.	A method, system, storage medium, and terminal for NAND flash instruction combination verification (一種非型閃存指令組合驗證方法、系統、儲存介質和終端).	Inventory Patent	Our Company	PRC	ZL202010605507.5	16 October 2020	28 June 2040
19.	A high-speed SPI command response circuit applied to FLASH (一種應用於FLASH的高速SPI指令應答電路).	Inventory Patent	Our Company	PRC	ZL202010613528.1	16 October 2020	29 June 2040
20.	Flash memory chip and method for reading the same (Flash芯片及其讀方法).	Inventory Patent	Our Company	PRC	ZL20191138851.7	20 October 2020	29 December 2039
21.	A counting method for enhanced flash and the enhanced flash memory (增強型flash的計數方法及增強型flash)	Inventory Patent	Our Company	PRC	ZL201911389103.0	20 October 2020	29 December 2039
22.	A method, device, and chip for reducing the core area of non-volatile flash memory (一種減小非易失型閃存核心尺寸的方法、裝置及芯片).	Inventory Patent	Our Company	PRC	ZL202010549603.2	16 March 2021	15 June 2040
23.	A method, system, apparatus, and storage medium for Nor flash configuration module verification (一種Nor flash配置模塊驗證方法、系統、裝置和儲存介質).	Inventory Patent	Our Company	PRC	ZL201911412409.3	27 October 2020	30 December 2039
24.	A method and apparatus for analog-digital mixed-signal verification of Nor Flash (一種Nor Flash的數模混合驗證方法及裝置).	Inventory Patent	Our Company	PRC	ZL201911407925.7	3 November 2020	30 December 2039
25.	A method for programming a flash memory device (一種閃存設備的編程方法).	Inventory Patent	Our Company	PRC	ZL202010483301.X	25 December 2020	31 May 2040
26.	Non-volatile flash memory deep sleep low quiescent power circuit (非易失型閃存深睡眠低靜態功耗的電路)	Inventory Patent	Our Company	PRC	ZL202011117308.6	15 January 2021	18 October 2040

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
27.	Method and apparatus for shortening the erase time (縮短擦除時間的方法及裝置)	Inventory Patent	Our Company	PRC	ZL201911389699.4	9 February 2021	29 December 2039
28.	Wide operating voltage low power, high-drive-strength pump circuit and non-volatile memory (寬電壓低功耗強驅動能力泵電路及非易失性存儲器)	Inventory Patent	Our Company	PRC	ZL202011298169.1	23 February 2021	17 November 2040
29.	Method, circuit, storage medium, and terminal for reducing read current in non-volatile flash memory (非易失型閃存降低讀電流的方法、電路、儲存介質和終端)	Inventory Patent	Our Company	PRC	ZL202011279293.3	2 March 2021	15 November 2040
30.	A method, system, storage medium, and terminal for overcoming erase interference (一種克服擦除干擾的方法、系統、儲存介質和終端)	Inventory Patent	Our Company	PRC	ZL202010605503.7	5 March 2021	28 June 2040
31.	A method, system, storage medium, and terminal for mitigating Vt shift during repeated erase-program operations (改善多次擦除編程Vt偏移方法、系統、儲存介質和終端)	Inventory Patent	Our Company	PRC	ZL202010548355.X	17 August 2021	15 June 2040
32.	NOR/NAND flash memory digital verification method, system, storage medium, and terminal (應答式或非型閃存數字驗證方法、系統、儲存介質和終端)	Inventory Patent	Our Company	PRC	ZL202010612267.1	16 March 2021	29 June 2040
33.	Method, system, storage medium, and terminal for reducing NAND flash memory programming time (減少非型閃存編程時間的方法、系統、儲存介質和終端)	Inventory Patent	Our Company	PRC	ZL202010618632.X	16 March 2021	30 June 2040
34.	Method, circuit, storage medium, and terminal for implementing a NAND flash memory interface circuit (非型閃存介面電路的實現方法、電路、儲存介質和終端)	Inventory Patent	Our Company	PRC	ZL202010618633.4	19 March 2021	30 June 2040
35.	Method, system, storage medium, and terminal for reducing erase interference and erase time (降低擦除干擾和擦除時間的方法、系統、儲存介質及終端)	Inventory Patent	Our Company	PRC	ZL202010604140.5	23 March 2021	28 June 2040

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
36.	Method, apparatus, storage medium, and terminal for fault location analysis of a storage cell (存儲單元的故障定位分析方法、裝置、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202011475437.2	23 March 2021	14 December 2030
37.	A circuit and chip for multiplexing an oscillator frequency adjustment module and a reference module (一種複用振蕩器頻率調整模塊和基準模塊的電路及芯片).	Inventory Patent	Our Company	PRC	ZL202011515026.1	30 March 2021	20 December 2040
38.	Method, system, storage medium, and terminal for reducing over-erase phenomenon and erase time (降低過擦除現象和擦除時間方法、系統、存儲介質及終端).	Inventory Patent	Our Company	PRC	ZL202010597006.7	6 April 2021	27 June 2040
39.	An oscillator and chip (一種振盪器及芯片).	Utility Model	Our Company	PRC	ZL202022209604.0	6 April 2021	29 September 2030
40.	A circuit and chip for reducing the area of a column redundancy replacement circuit (一種減小列冗餘替換電路面積的電路及芯片).	Inventory Patent	Our Company	PRC	ZL202011141934.9	16 April 2021	21 October 2040
41.	A data output driving circuit and non-volatile flash memory (一種數據輸出驅動電路及非易失型閃存器)	Inventory Patent	Our Company	PRC	ZL202011443166.2	16 April 2021	10 December 2040
42.	A circuit and chip for overcoming erase interference (一種克服擦除干擾的電路及芯片).	Utility Model	Our Company	PRC	ZL202022347008.9	8 June 2021	19 October 2030
43.	An oscillator and chip (一種振盪器及芯片).	Utility Model	Our Company	PRC	ZL202022205339.9	6 July 2021	29 September 2030
44.	A parallel-to-serial data output circuit (一種併行數據轉串行輸出電路)	Utility Model	Our Company	PRC	ZL202022882247.4	6 July 2021	3 December 2030
45.	A circuit enabling rapid oscillation stabilization and flash memory chip (一種振盪器啟用快速振盪穩定的電路及flash芯片).	Utility Model	Our Company	PRC	ZL202023009540.6	6 July 2021	14 December 2030
46.	A charge pump circuit and flash memory chip (一種電荷泵電路及flash芯片) . . .	Utility Model	Our Company	PRC	ZL202023158325.2	6 July 2021	23 December 2030
47.	A low-power, high-speed sense amplifier circuit and memory (一種低功耗快速敏感放大器電路及存儲器).	Utility Model	Our Company	PRC	ZL202023244246.3	9 July 2021	28 December 2030

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
48.	A storage cell array for highly reliable non-volatile memory and the non-volatile memory device (高可靠的非易失存儲器的存儲單元陣列及非易失存儲器).	Utility Model	Our Company	PRC	ZL202023237578.9	16 July 2021	28 December 2030
49.	A circuit for enhancing Flash chip erase efficiency and the Flash chip (提升Flash芯片擦除效率的電路和Flash芯片).	Inventory Patent	Our Company	PRC	ZL202011577919.9	3 August 2021	27 December 2040
50.	Chip power-on reset method and chip (芯片上電複位方法及芯片).	Inventory Patent	Our Company	PRC	ZL202010547934.2	23 October 2020	15 June 2040
51.	A temperature-compensated oscillator and chip (一種隨溫度變化的振盪器及芯片).	Inventory Patent	Our Company	PRC	ZL202011061100.7	27 August 2021	29 September 2040
52.	A test tool for preventing chip damage from repeated BGA149 soldering operations (一種避免重複焊接BGA149導致芯片損壞的測試工具)	Utility Model	Our Company	PRC	ZL202023242423.4	27 August 2021	28 December 2030
53.	A low voltage alarm circuit for a non-volatile chip and the non-volatile chip (一種非易失型芯片的低電壓報警電路及非易失型芯片).	Utility Model	Our Company	PRC	ZL202023242440.8	27 August 2021	28 December 2030
54.	A power-on and power-down detection circuit and integrated circuit (一種上電和掉電檢測電路、集成電路)	Utility Model	Our Company	PRC	ZL202023289031.3	27 August 2021	29 December 2030
55.	A circuit for high-speed ID and chip status reading, and flash memory (一種高速讀ID和芯片狀態的電路和flash存儲器) . .	Inventory Patent	Our Company	PRC	ZL202011632894.8	31 August 2021	30 December 2040
56.	Method, system, storage medium, and terminal for reducing NAND flash memory programming pump area (減少非型閃存編程泵面積的方法、系統、儲存介質和終端).	Inventory Patent	Our Company	PRC	ZL202010524808.5	10 September 2021	9 June 2040
57.	A circuit and non-volatile flash memory chip for reducing the non-volatile flash memory chip area (減小非易失性閃存芯片面積的電路及非易失性閃存芯片) . .	Inventory Patent	Our Company	PRC	ZL202011604743.1	14 September 2021	29 December 2040

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
58.	A method, apparatus, storage medium, and terminal for checking power-on parameters of non-volatile flash memory (非易失型閃存上電參數檢查方法、裝置、儲存介質和終端).	Inventory Patent	Our Company	PRC	ZL202011614386.7	21 September 2021	29 December 2040
59.	An FPGA-based high-precision flash read/write timing acquisition device (一種基於FPGA的高精度flash擦寫時間獲取裝置).	Inventory Patent	Our Company	PRC	ZL202011632921.1	24 September 2021	30 December 2040
60.	A method, apparatus, storage medium, and terminal for recording whether power failure occurred during erasure (記錄是否有擦除時掉電的方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202011141943.8	8 October 2021	21 October 2040
61.	Method, apparatus, storage medium, and terminal for backup cell replacement circuit verification (備份cell替換電路驗證方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202011554831.5	29 October 2021	23 December 2040
62.	A method, apparatus, storage medium, and terminal for testing SD NAND (SD NAND測試方法、裝置、儲存介質和終端).	Inventory Patent	Our Company	PRC	ZL202011589823.4	29 October 2021	28 December 2040
63.	Non-volatile memory instruction combination verification method, apparatus, storage medium, and terminal (非易失存儲器指令組合驗證方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202011407586.5	5 November 2021	3 December 2040
64.	A method, apparatus, storage medium, and terminal for real modeling verification of a memory (一種存儲器的真實建模驗證方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202011552567.1	9 November 2021	23 December 2040
65.	A circuit for alleviating insufficient driving capability during instant startup of a chip in active mode (緩解芯片active模式啓動瞬間驅動能力不足的電路).	Inventory Patent	Our Company	PRC	ZL202011614047.9	12 November 2021	29 December 2040
66.	A parallel flash memory lifetime testing apparatus (一種並行的flash壽命測試裝置).	Inventory Patent	Our Company	PRC	ZL202011619489.2	23 November 2021	30 December 2040

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
67.	A method, apparatus, storage medium, and terminal for over-erasure verification based on real modelling (基於真實建模的過擦除驗證方法、裝置、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202011554822.6	30 November 2021	23 December 2040
68.	A Flash (一種Flash)	Utility Model	Our Company	PRC	ZL202121342192.6	30 November 2021	15 June 2031
69.	A method, apparatus, storage medium, and terminal for fault injection verification of a memory based on real modelling (存儲器的真實建模注錯驗證方法、裝置、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202011554832.X	14 December 2021	23 December 2040
70.	Nor Flash memory circuit and Nor Flash (Nor Flash存儲器電路和Nor Flash)	Utility Model	Our Company	PRC	ZL202121458641.3	14 December 2021	28 June 2031
71.	A method, apparatus, electronic device, and storage medium for non-volatile memory programming (非易失性存儲器編程方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202110729079.1	15 December 2023	28 June 2041
72.	A method, system, storage medium, and terminal for transparent capacity expansion of FLASH memory (用於FLASH的無感擴容方法、系統、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202010554179.0	21 December 2021	16 June 2040
73.	A small-size Latch cell circuit and Flash chip (一種小尺寸Latch單元電路及Flash芯片)	Inventory Patent	Our Company	PRC	ZL202011535598.6	21 December 2021	22 December 2040
74.	A discharge circuit for a negative voltage charge pump and non-volatile memory (一種負壓電荷泵的放電電路及非易失型儲存器)	Inventory Patent	Our Company	PRC	ZL202011552574.1	4 January 2022	23 December 2040
75.	A NOR MCP memory chip (一種NOR MCP存儲芯片)	Utility Model	Our Company	PRC	ZL202121473306.0	25 January 2022	29 June 2031
76.	A circuit for speeding up oscillator establishment (一種加快振盪器建立的電路)	Utility Model	Our Company	PRC	ZL202121470916.5	28 January 2022	29 June 2031

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
77.	A method, apparatus, storage medium, and terminal for optimizing and accelerating memory simulation verification (優化加快存儲器仿真驗證方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202011575615.9	1 February 2022	27 December 2040
78.	A reset circuit for a charge amplifier and a method for obtaining the reset time (一種電荷放大器的複位電路及複位時間獲取方法).	Inventory Patent	Our Company	PRC	ZL202010490107.4	15 February 2022	1 June 2040
79.	An oscillator circuit and flash chip (一種振盪器電路及flash芯片)	Inventory Patent	Our Company	PRC	ZL202011479827.7	18 February 2022	14 December 2040
80.	A charge pump circuit and non-volatile memory (一種電荷泵電路及非易失性存儲器).	Inventory Patent	Our Company	PRC	ZL202011604742.7	8 March 2022	29 December 2040
81.	A boost circuit with a pre-charge function and a charge pump circuit (一種具有預充電功能的升壓電路及電荷泵電路) . .	Utility Model	Our Company	PRC	ZL202220686269.X	10 May 2022	27 March 2032
82.	A parallel-to-serial output circuit in DTR mode (一種DTR模式下的併轉串輸出電路).	Utility Model	Our Company	PRC	ZL202123346106.1	24 May 2022	27 December 2031
83.	A method for custom display of to-do data (一種自定義待辦數據的展示方法) . . .	Inventory Patent	SiliconBay	PRC	ZL202111648636.3	29 April 2025	29 December 2041
84.	A POR circuit with high power-down POR voltage (一種高掉電POR電壓的POR電路).	Inventory Patent	Our Company	PRC	ZL202110737175.0	14 June 2022	29 June 2041
85.	A charge pump circuit and control method and memory (電荷泵電路及其控制方法、存儲器).	Inventory Patent	Our Company	PRC	ZL202110736960.4	8 July 2022	29 June 2041
86.	A method, apparatus, electronic device, and storage medium for verifying a suspend function (一種掛起功能的驗證方法、裝置、電子設備及存儲介質) . .	Inventory Patent	Our Company	PRC	ZL202210438911.7	8 July 2022	24 April 2042
87.	A frame-packaged SD NAND (一種基於框架封裝的SD NAND)	Utility Model	Our Company	PRC	ZL202121444025.2	12 July 2022	27 June 2031
88.	A method, apparatus, electronic device, and storage medium for generating a parity check matrix (一種校驗矩陣生成方法、裝置、電子設備及存儲介質) . .	Inventory Patent	Our Company	PRC	ZL202111386408.3	5 August 2022	21 November 2041

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
89.	A charge pump discharge method, circuit, system, electronic device and storage medium (一種電荷泵放電方法、電路、系統、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202110719871.9	12 August 2022	27 June 2031
90.	A power consumption measuring apparatus (一種功耗測量裝置)	Utility Model	Our Company	PRC	ZL202220859421.X	16 August 2022	13 April 2032
91.	A method, apparatus, and flash memory for testing flash memory programming (用於測試閃速存儲器的編程方法、裝置及閃速存儲器).	Inventory Patent	Our Company	PRC	ZL202210654745.4	30 August 2022	9 June 2042
92.	Nor Flash memory circuit and Nor Flash memory (Nor Flash存儲器電路和Nor Flash).	Utility Model	Our Company	PRC	ZL202121443287.7	27 September 2022	27 June 2031
93.	A charge pump for non-volatile memory (一種用於非易失性存儲器的電荷泵)	Utility Model	Our Company	PRC	ZL202220859083.X	14 October 2022	13 April 2032
94.	Power-down detection circuit	Inventory Patent	Our Company	Germany, France, the United Kingdom, Lithuania	EP3879278	26 October 2022	10 November 2040
95.	Programmable power supply test system, simulation method, apparatus, storage medium, and terminal (可編程電源測試系統、模擬方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202110672574.3	18 November 2022	16 June 2041
96.	Flash memory bad storage unit test method, apparatus, equipment, and storage medium (閃存的壞存儲單元測試方法、裝置、設備及存儲介質)	Inventory Patent	Shanghai XCTX; Our Company	PRC	ZL202111386381.8	18 November 2022	21 November 2041
97.	Counting address acquisition method, counting method, apparatus, equipment, and storage medium (計數地址獲取方法、計數方法、裝置、設備及存儲介質)	Inventory Patent	Shanghai XCTX; Our Company	PRC	ZL202111640339.4	18 November 2022	28 December 2041
98.	A compatible pad and electronic circuit (一種兼容焊盤及電子電路)	Inventory Patent	Our Company	PRC	ZL202123421800.5	24 May 2022	30 December 2031
99.	A method, apparatus, electronic device, and storage medium for reading a memory chip (一種存儲芯片的讀取方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202211230101.9	13 December 2022	29 September 2042

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
100.	Nor Flash memory full-chip erase method, apparatus, equipment, and medium (Nor Flash的全片擦除方法、裝置、設備及介質)	Inventory Patent	Our Company	PRC	ZL202211229125.2	13 December 2022	29 September 2042
101.	Nor Flash erase method, apparatus, equipment, and medium (Nor Flash的擦除方法、裝置、設備及介質)	Inventory Patent	Our Company	PRC	ZL202211229128.6	13 December 2022	29 September 2042
102.	A post-programming method, erasing method, apparatus, electronic device, and storage medium (一種後編程方法、擦除方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202211229109.3	13 December 2022	29 September 2042
103.	Flash memory chip erase voltage configuration method, apparatus, equipment, and storage medium (閃存芯片的擦除電壓配置方法、裝置、設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202211229121.4	13 December 2022	29 September 2042
104.	Flash memory chip configuration information reading method, apparatus, electronic device, and storage medium (閃存芯片配置信息讀取方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202211229124.8	13 December 2022	29 September 2042
105.	A method, apparatus, electronic device, and storage medium for erasure with low erase damage (一種低擦除損傷的擦除方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202211230102.3	13 December 2022	29 September 2042
106.	Flash memory chip erase operation voltage update method, apparatus, equipment, and medium (閃存芯片的擦除操作電壓的更新方法、裝置、設備及介質)	Inventory Patent	Our Company	PRC	ZL202211229127.1	13 December 2022	29 September 2042
107.	Flash memory chip suspend function verification method, apparatus, equipment, and medium (閃存芯片掛起功能的驗證方法、裝置、設備及介質)	Inventory Patent	Our Company	PRC	ZL202211230100.4	13 December 2022	29 September 2042
108.	Flash memory chip suspend function verification method, apparatus, equipment, and medium (閃存芯片掛起功能的驗證方法、裝置、設備及介質)	Inventory Patent	Our Company	PRC	ZL202211229131.8	16 December 2022	29 September 2042

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
109.	A method for reading and writing a memory chip, electronic device, and storage medium (一種存儲芯片的讀寫方法、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202211230098.0	16 December 2022	29 September 2042
110.	Configuration information storage circuit, volatile configuration method, apparatus, and flash memory (配置信息存儲電路、易失性配置方法、裝置及閃速存儲器) .	Inventory Patent	Our Company	PRC	ZL202211230097.6	10 January 2023	29 September 2042
111.	An inverter circuit used for an oscillator, the oscillator, and a charge pump circuit (一種用於振盪器的反相器電路、振盪器及電荷泵電路).	Utility Model	Our Company	PRC	ZL202223043340.1	17 March 2023	15 November 2032
112.	Nor Flash full-chip erasure method, apparatus, equipment, and medium (Nor Flash的全片擦除方法、裝置、設備及介質).	Inventory Patent	Our Company	PRC	ZL202211229126.7	24 March 2023	29 September 2042
113.	A low-noise active filter circuit, bandgap reference circuit, and power management chip (低噪聲的有源濾波電路、帶隙基準電路及電源管理芯片) . .	Utility Model	Chengdu Bohr Micro	PRC	ZL202223500178.1	28 March 2023	25 December 2032
114.	An inverter circuit used for an oscillator, the oscillator, and a charge pump circuit (一種用於振盪器的反相器電路、振盪器及電荷泵電路).	Utility Model	Our Company	PRC	ZL202223043400.X	4 April 2023	15 November 2032
115.	A Flash chip packaging structure (一種Flash芯片封裝結構)	Utility Model	Our Company	PRC	ZL202222972597.9	7 April 2023	7 November 2032
116.	Chip select enable control apparatus, reading apparatus, erase/write apparatus, and flash memory (片選使能控制裝置、讀取裝置、擦寫裝置及快閃存儲器) . .	Inventory Patent	Our Company	PRC	ZL202310016973.3	2 May 2023	5 January 2043
117.	Nor Flash with transparent capacity expansion, sensing circuit, and electronic equipment (無感擴容的Nor Flash、感知電路及電子設備)	Inventory Patent	Our Company	PRC	ZL202310016992.6	9 May 2023	5 January 2043
118.	A sample-and-hold circuit, sample-and-hold method, apparatus, and current detection circuit (採樣保持電路、採樣保持方法、裝置及電流檢測電路).	Inventory Patent	Chengdu Bohr Micro	PRC	ZL202310017267.0	12 May 2023	5 January 2043

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
119.	A method, apparatus, storage medium, and terminal for checking erase/write data of a non-volatile chip (非易失芯片擦寫數據檢查方法、裝置、存儲介質和終端) .	Inventory Patent	Our Company	PRC	ZL202011552573.7	26 May 2023	23 December 2040
120.	Programming pulse width adjustment circuit, adjustment method, programming circuit, and flash memory (編程脈寬調節電路、調節方法、編程電路及快閃存儲器).	Inventory Patent	Our Company	PRC	ZL202111392226.7	2 June 2023	18 November 2041
121.	A method, apparatus, equipment, and storage medium for reading chip configuration file information (讀取芯片配置文件信息的方法、裝置、設備及存儲介質).	Inventory Patent	Our Company	PRC	ZL202211491412.0	2 June 2023	24 November 2042
122.	A method, apparatus, storage medium, and terminal for non-volatile chip strong 0 repair verification (非易失芯片強0修復驗證方法、裝置、存儲介質和終端) . .	Inventory Patent	Our Company	PRC	ZL202011554835.3	23 June 2023	23 December 2040
123.	A method, apparatus, storage medium, and terminal for internal single-step testing of a non-volatile chip (非易失型芯片內部單步測試方法、裝置、存儲介質、終端).	Inventory Patent	Our Company	PRC	ZL202011589882.1	23 June 2023	28 December 2040
124.	A method, apparatus, electronic device, and storage medium for voltage switching for a chip (用於芯片的電壓切換方法、裝置、電子設備及存儲介質) .	Inventory Patent	Our Company	PRC	ZL202110719890.1	4 July 2023	27 June 2041
125.	Flash memory erase interrupt recovery test method, apparatus, electronic device, and storage medium (閃存擦除中斷恢復測試方法、裝置、電子設備及存儲介質).	Inventory Patent	Our Company	PRC	ZL202110719195.5	4 July 2023	27 June 2041
126.	Power failure detection circuit	Inventory Patent	Our Company	United States	US11703526B2	18 July 2023	10 November 2040
127.	A FLASH memory with an SPI interface for high-speed data reading (一種高速讀取數據的SPI接口的FLASH存儲器). . .	Inventory Patent	Our Company	PRC	ZL202011604951.1	25 July 2023	29 December 2040

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
128.	A wafer test data analysis method, platform, electronic device, and storage medium (晶圓測試數據的分析方法、平台、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202110565923.1	25 July 2023	23 May 2041
129.	A clamp voltage generation circuit, reading circuit, and non-volatile memory (一種鉗位電壓產生電路、讀取電路及非易失性存儲器).	Utility Model	Shanghai XCTX	PRC	ZL202320605582.0	25 July 2023	23 March 2033
130.	A hysteresis circuit, power-on reset circuit, and flash memory (一種遲滯電路、上電復位電路及閃速存儲器).	Utility Model	Shanghai XCTX	PRC	ZL202320819744.0	25 July 2023	12 April 2033
131.	A reference current generation circuit, method, electronic equipment, and test fixture (一種基準電流產生電路、方法、電子設備及測試工裝).	Inventory Patent	Our Company	PRC	ZL202110736049.3	4 August 2023	29 June 2041
132.	A flash memory verification and repair method, apparatus, and electronic equipment (一種閃存的校驗修復方法、裝置和電子設備).	Inventory Patent	Our Company	PRC	ZL202110734953.0	4 August 2023	29 June 2041
133.	Multi-die stacked package memory and output synchronization method thereof .	Inventory Patent	Our Company	United States	US11735229B2	22 August 2023	10 November 2040
134.	A method, apparatus, storage medium, and terminal for reducing the probability of read errors after power failure (減少掉電後讀錯誤幾率的方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202110558998.7	25 August 2023	20 May 2041
135.	Nor Flash writing method, apparatus, programming circuit, and equipment (Nor Flash的寫入方法、裝置、編程電路及設備).	Inventory Patent	Shanghai XCTX	PRC	ZL202310557176.6	25 August 2023	16 May 2043
136.	High-side driving method, apparatus, and circuit for an N-type dual H-bridge motor driver chip (N型雙H 橋電機驅動芯片的高邊驅動方法、裝置和電路) . .	Inventory Patent	Chengdu Bohr Micro	PRC	ZL202310669361.4	25 August 2023	6 June 2043
137.	Nor Flash reading method, apparatus, storage chip, and equipment (Nor Flash的讀取方法、裝置、存儲芯片及設備) .	Inventory Patent	Our Company; Shanghai XCTX	PRC	ZL202310766847.X	25 August 2023	26 June 2043

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
138.	A clock latch circuit with reset and low delay, and a chip (一種帶複位且延時少的時鐘鎖存器電路及芯片)	Inventory Patent	Our Company	PRC	ZL202110672593.6	29 August 2023	16 June 2041
139.	SPI Nor Flash test platform, test method, test apparatus, and electronic equipment (SPI Nor Flash測試平台、測試方法、測試裝置和電子設備).	Inventory Patent	Our Company	PRC	ZL202110736016.9	8 September 2023	29 June 2041
140.	A fast reading circuit for a memory chip, memory chip, and electronic device (一種用於存儲芯片的快速讀取電路、存儲芯片及電子設備).	Inventory Patent	Our Company; Shanghai XCTX	PRC	ZL202310804372.9	15 September 2023	2 July 2043
141.	Serial interface NAND memory chip and method for reading data therefrom (串行接口NAND存儲芯片及從其中讀取數據的方法).	Inventory Patent	Our Company	PRC	ZL202011036444.2	26 September 2023	26 September 2040
142.	Nor Flash reset method, apparatus, memory chip, and equipment (Nor Flash的複位方法、裝置、存儲芯片及設備) .	Inventory Patent	Our Company; Shanghai XCTX	PRC	ZL202310863763.8	26 September 2023	13 July 2043
143.	A chip edge cracking detection circuit and memory chip (一種芯片崩邊檢測電路及存儲芯片).	Inventory Patent	Our Company	PRC	ZL202310888038.6	10 October 2023	18 July 2043
144.	Nor Flash reading method, apparatus, storage chip, and equipment (Nor Flash的讀取方法、裝置、存儲芯片及設備) .	Inventory Patent	Our Company; Shanghai XCTX	PRC	ZL202310766806.0	13 October 2023	26 June 2043
145.	Erasure method for a small capacity memory array and decoding circuit (小容量存儲陣列的擦除方法和解碼電路) .	Inventory Patent	Our Company	PRC	ZL202310888172.6	13 October 2023	18 July 2043
146.	A method, apparatus, storage medium, and terminal for improving chip verification efficiency (一種提升芯片驗證效率的方法、裝置、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202011495599.2	24 October 2023	16 December 2040
147.	Nor Flash reading method, apparatus, storage chip, and equipment (Nor Flash讀取方法、裝置、存儲芯片及設備) . .	Inventory Patent	Our Company; Shanghai XCTX	PRC	ZL202310804308.0	31 October 2023	2 July 2043
148.	An over-erasure processing method and apparatus for a novel non-volatile memory (一種新型非易失性存儲器的過擦除處理方法和裝置).	Inventory Patent	Our Company	PRC	ZL201810637809.3	3 November 2023	19 June 2038

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
149.	A circuit rapidly established by reference to current and method (一種參考電流快速建立電路及方法).	Inventory Patent	Our Company; Shanghai XCTX	PRC	ZL202310804431.2	3 November 2023	2 July 2043
150.	Flash memory redundancy replacement method, apparatus, register, and storage chip (flash的冗餘替換方法、裝置、寄存器和存儲芯片).	Inventory Patent	Our Company	PRC	ZL202310888219.9	10 November 2023	18 July 2043
151.	Flash chip erasure method, apparatus, and flash chip (flash芯片的擦除方法、裝置及flash芯片).	Inventory Patent	Shanghai XCTX	PRC	ZL202311145380.3	5 December 2023	5 September 2043
152.	An oscillator circuit and memory chip (一種振盪器電路及存儲芯片)	Inventory Patent	Our Company	PRC	ZL202310888188.7	8 December 2023	18 July 2043
153.	A method, apparatus, storage medium, and terminal for erasing a non-volatile memory (一種非易失型存儲器擦除方法、裝置、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202110607474.2	15 December 2023	31 May 2041
154.	Parity check current setting method, operation check method, and related equipment (校驗電流的設置方法、操作校驗方法及相關設備).	Inventory Patent	Shanghai XCTX	PRC	ZL202311217493.X	15 December 2023	19 September 2043
155.	Operation time simulation acquisition method, apparatus, electronic device, and storage medium (操作時間仿真獲取方法、裝置、電子設備及存儲介質)	Inventory Patent	Shanghai XCTX	PRC	ZL202311145378.6	22 December 2023	5 September 2043
156.	정전 검출 회로POWER-DOWN DETECTION CIRCUIT	Inventory Patent	Our Company	South Korea	1026288430000	25 January 2024	10 November 2040
157.	A method for delayed bias voltage establishment, bias circuit, comparator, and integrated circuit (延遲偏置電壓建立的方法、偏置電路、比較器和集成電路).	Inventory Patent	Our Company	PRC	ZL202310874381.5	26 January 2024	16 July 2043
158.	A clock output method, circuit, and chip (一種時鐘輸出方法、電路及芯片)	Inventory Patent	Our Company	PRC	ZL202310881495.2	30 January 2024	17 July 2043
159.	Threshold voltage acquisition system, transfer method, apparatus, equipment, and storage medium (閾值電壓的獲取系統、傳遞方法、裝置、設備及存儲介質).	Inventory Patent	Our Company	PRC	ZL202110719339.7	2 February 2024	27 June 2041

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No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
160.	A method, apparatus, electronic device, and storage medium for erasure with low erase damage (一種低擦除損傷的擦除方法、裝置、電子設備及存儲介質) .	Inventory Patent	Our Company	PRC	ZL202110736052.5	2 February 2024	29 June 2041
161.	Erase/write interference test system, method, and execution apparatus (擦寫干擾測試系統、方法以及執行裝置) . .	Inventory Patent	Our Company	PRC	ZL202110737988.X	2 February 2024	29 June 2041
162.	A method, apparatus, electronic device, and storage medium for acquiring an erase time (一種擦除時間的獲取方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202110737200.5	2 February 2024	29 June 2041
163.	A method, apparatus, and electronic device for accelerating Nor Flash programming speed (加快Nor Flash編程速度的方法、裝置、電子設備).	Inventory Patent	Our Company	PRC	ZL202110728044.6	6 February 2024	28 June 2041
164.	Erase interference detection method, repair method, apparatus, chip, and electronic equipment (擦除干擾檢測方法、修復方法、裝置、芯片及電子設備)	Inventory Patent	Our Company	PRC	ZL202311152176.4	6 February 2024	6 September 2043
165.	A method for chip voltage establishment, command execution method, apparatus, chip, and equipment (芯片的電壓建立方法、命令執行方法、裝置、芯片及設備).	Inventory Patent	Shanghai XCTX	PRC	ZL202311352776.5	6 February 2024	18 October 2043
166.	A method, apparatus, storage medium, and terminal for improving data channel speed (一種提升數據通道速度的方法、裝置、存儲介質和終端).	Inventory Patent	Our Company	PRC	ZL202110672497.1	23 February 2024	16 June 2041
167.	A method, apparatus, electronic device, and storage medium for suppressing flash memory over-erasure (一種抑制閃存過擦除的方法、裝置、電子設備及存儲介質).	Inventory Patent	Our Company	PRC	ZL202110737206.2	12 March 2024	29 June 2041
168.	A method, apparatus, electronic device, and storage medium for simultaneously programming multiple blocks (一種對多區塊同時編程的方法裝置、電子設備及存儲介質).	Inventory Patent	Our Company	PRC	ZL202110728045.0	15 March 2024	28 June 2041

APPENDIX VI STATUTORY AND GENERAL INFORMATION

No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
169.	A method, apparatus, electronic device, and storage medium for non-volatile memory erasure (非易失性存儲器擦除方法、裝置、電子設備及存儲介質) . . .	Inventory Patent	Our Company	PRC	ZL202110729052.2	15 March 2024	28 June 2041
170.	An oscillator enable circuit, oscillator circuit, and charge pump circuit (一種振盪器使能電路、振盪器電路及電荷泵電路)	Utility Model	Our Company	PRC	ZL202322346243.8	15 March 2024	29 August 2033
171.	Programming verification voltage setting method, programming method, apparatus, chip, and equipment (編程校驗電壓設定方法、編程方法、裝置、芯片及設備)	Inventory Patent	Shanghai XCTX	PRC	ZL202410003711.8	26 March 2024	1 January 2044
172.	A method, circuit, storage medium, and terminal for detecting flash memory errors (檢測flash存儲出錯的方法、電路、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202011614403.7	12 April 2024	29 December 2040
173.	A reference voltage measurement apparatus for a memory chip and the memory chip (一種用於存儲芯片的基準電壓測量裝置及存儲芯片)	Utility Model	Our Company	PRC	ZL202322346242.3	16 April 2024	29 August 2033
174.	A method, chip, and equipment for life record of SPI NAND (一種用於SPI NAND的壽命記錄方法、芯片及設備)	Inventory Patent	Our Company	PRC	ZL202311685976.2	11 June 2024	10 December 2043
175.	An oscillator that varies with power supply voltage and a chip (一種隨電源電壓變化的振盪器及芯片)	Inventory Patent	Our Company	PRC	ZL202011062086.2	25 June 2024	29 September 2040
176.	A method, apparatus, electronic device, and storage medium for randomized verification of voltage configuration (電壓配置的隨機化驗證方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202310874274.2	5 July 2024	16 July 2042
177.	A method, apparatus, storage medium, and terminal for on-chip CRC checking data integrity (片內CRC檢查數據完整性方法、裝置、存儲介質和終端)	Inventory Patent	Our Company	PRC	ZL202011193697.0	19 July 2024	29 October 2040
178.	A dead time generation apparatus and timer differential output circuit (一種死區產生裝置及定時器差分輸出電路)	Utility Model	Our Company	PRC	ZL202420283884.5	17 September 2024	5 February 2034

APPENDIX VI STATUTORY AND GENERAL INFORMATION

No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
179.	NAND FLASH group swapping method, apparatus, equipment, and medium (NAND FLASH分組調換方法、裝置、設備及介質)	Inventory Patent	Our Company	PRC	ZL202210594820.2	5 November 2024	26 May 2042
180.	A clock frequency test method, apparatus, electronic device, and storage medium (一種時鐘頻率測試方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202111388281.9	4 March 2025	21 November 2041
181.	A substrate-based packaging structure SDNAND (一種基於基板式封裝結構的SDNAND)	Utility Model	Our Company	PRC	ZL202323203781.8	4 March 2025	26 November 2033
182.	A method, apparatus, electronic device, and storage medium for reliability testing of flash memory chips (閃存芯片的可靠性測試方法、裝置、電子設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202111628666.8	25 April 2025	27 December 2041
183.	Count value reading method, counting method, apparatus, electronic device, and storage medium (計數值讀取方法、計數方法、裝置、電子設備及存儲介質)	Inventory Patent	Shanghai XCTX; Our Company	PRC	ZL202111671094.1	6 December 2022	30 December 2041
184.	Power on/off error detection system, method, control terminal, and apparatus (開關機出錯偵測系統、方法及控制終端、裝置)	Inventory Patent	Our Company	PRC	ZL202111384006.X	6 May 2025	18 November 2041
185.	A chip solidification method, apparatus, equipment, and storage medium for improving wafer utilization rate (提高晶圓利用率的芯片固化方法、裝置、設備及存儲介質)	Inventory Patent	Our Company	PRC	ZL202111628636.7	10 June 2025	27 December 2041
186.	An LED display system, apparatus, and method (一種LED顯示系統、裝置及方法)	Inventory Patent	Our Company	PRC	ZL202310427924.9	27 June 2025	19 April 2043
187.	A global configuration programming method, apparatus, and system (一種全域配置編程方法、裝置及系統)	Inventory Patent	Our Company	PRC	ZL202111402017.6	11 July 2025	18 November 2041
188.	Erase verification method for a small capacity memory array, erasure method, and decoding circuit (小容量存儲陣列的擦除校驗方法、擦除方法和解碼電路)	Inventory Patent	Our Company	PRC	ZL202111391835.0	15 July 2025	18 November 2041

APPENDIX VI STATUTORY AND GENERAL INFORMATION

No.	Name of Patent	Patent Type	Patentee	Place of registration	Patent number	Registration date	Expiry date
189.	Flash memory chip programming method, apparatus, system, electronic device, and storage medium (閃存芯片編程方法、裝置、系統、電子設備及存儲介質) . . .	Inventory Patent	Our Company	PRC	ZL202111398342.X	5 August 2025	18 November 2041
190.	Nor Flash verification method, apparatus, equipment, and storage medium (Nor Flash的驗證方法、裝置、設備及存儲介質)	Inventory Patent	Shanghai XCTX	PRC	ZL202310242999.X	8 August 2025	13 March 2043
191.	A method, apparatus, equipment, and medium for reading startup data within a flash memory (閃速存儲器內啟動數據的讀取方法、裝置、設備及介質) . . .	Inventory Patent	Our Company	PRC	ZL202210735785.1	15 August 2025	26 June 2042
192.	A voltage monitoring circuit with hysteresis characteristics (一種具有遲滯特性的電壓監測電路)	Inventory Patent	Our Company	PRC	ZL202210043109.8	12 September 2025	13 January 2042
193.	A method for improving Nor Flash data retention capability and related equipment (提高Nor Flash數據保持能力的方法及相關設備)	Inventory Patent	Our Company	PRC	ZL202510967839.0	12 September 2025	13 July 2045
194.	A word line selection circuit, memory array, and flash memory (一種字線選擇電路、存儲陣列和快閃存儲器)	Utility Model	Shanghai XCTX	PRC	ZL202422939656.1	26 September 2025	28 November 2034
195.	Method, apparatus, device, and storage medium for configuring erase voltage of flash memory chips (閃存芯片的擦除電壓配置方法、裝置、設備及存儲介質) .	Inventory Patent	Our Company	PRC	ZL202211677531.5	7 November 2025	25 December 2042
196.	A small-area, multiple column redundancy replacement method for NOR flash memory (一種針對NOR Flash的小面積、可多次列冗餘替換方法) . . .	Inventory Patent	Our Company	PRC	ZL202111635745.1	6 February 2026	28 December 2041
197.	Multi-die Stacked Package Memory and Output Synchronization Method thereof .	Invention	Our Company	Europe	EP3886097	7 January 2026	10 November 2040

(c) Copyrights

As of the Latest Practicable Date, we have registered the following copyrights in the PRC which, in the opinion of our Directors, are material to our business:

No.	Copyright	Type	Copyright owner	Registration number	Registration date
1	XMIS Sales Management System V1.0 (XMIS銷售管理系統V1.0) .	Software Copyright	Our Company	2020SR0401773	30 April 2020

APPENDIX VI STATUTORY AND GENERAL INFORMATION

No.	Copyright	Type	Copyright owner	Registration number	Registration date
2	XMIS Human Resources Management System V1.0 (XMIS 人事管理系統V1.0)	Software Copyright	Our Company	2020SR0623578	15 June 2020
3.	XMIS Warehouse Management System V1.0 (XMIS倉儲管理系統 V1.0)	Software Copyright	Our Company	2020SR0623144	15 June 2020
4.	XMIS Attendance Management System (PC Version) V1.0XMIS (XMIS考勤管理系統(PC端) V1.0)	Software Copyright	Our Company	2020SR0623572	15 June 2020
5.	XMIS IPD Project and Requirements Management System V1.0 (XMIS IPD項目和需求管理系統V1.0) . .	Software Copyright	Our Company	2020SR0623564	15 June 2020
6.	XMIS Office Automation System (XMIS辦公自動化系統V1.0) . . .	Software Copyright	Our Company	2020SR0623135	15 June 2020
7.	Xinzhijia APP Attendance Management System V1.1.4 (芯之家APP考勤管理系統V1.1.4).	Software Copyright	Our Company	2020SR0623112	15 June 2020
8.	XMIS User Permissions Management System V1.0 (XMIS 用戶和權限管理系統V1.0)	Software Copyright	Our Company	2020SR0623096	15 June 2020
9.	XMIS Financial Management System V1.0 (XMIS財務管理系統 V1.0)	Software Copyright	Our Company	2020SR0622924	15 June 2020
10.	XMIS Procurement and Outsourcing Management System V1.0 (XMIS 採購和委外管理系統 V1.0)	Software Copyright	Our Company	2020SR0622916	15 June 2020
11.	Xinzhijia CRM System V1.0 (芯之家CRM系統V1.0)	Software Copyright	SiliconBay	2021SR1681166	10 November 2021
12.	XTX.	Copyright	Our Company	Guo Zuo Deng Zi -2020-F-00968458	21 January 2020
13.	XT Motor Pilot Software (XT Motor Pilot 軟件)	Software Copyright	Our Company	2025SR1836678	22 September 2025
14.	XTX-IDE Software (XTX-IDE軟件).	Software Copyright	Our Company	2025SR1835856	22 September 2025
15.	XT Config Workbench Software (XT Config Workbench 軟件). . .	Software Copyright	Our Company	2025SR2080597	27 October 2025

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(d) Domain Names

As of the Latest Practicable Date, we had registered the following domain names which we consider to be material in relation to our business:

No.	Domain name	Registrant	Expiry date
1.	txtech.com	Our Company	31 July 2027
2.	txtech.cn	Our Company	25 December 2026
3.	txtech.com.cn	Our Company	25 December 2026
4.	txtech.net.cn	Our Company	25 December 2026
5.	txtech.org.cn	Our Company	25 December 2026
6.	x-semi.com	Our Company	2 October 2026

Save as aforesaid, as of the Latest Practicable Date, there were no other trademarks, patents or other intellectual or industrial property rights which we consider to be material in relation to our business.

C. FURTHER INFORMATION ABOUT OUR DIRECTORS AND SUBSTANTIAL SHAREHOLDERS

1. Disclosure of Interests

(a) Interests of our Directors and chief executive

Immediately following the completion of the [REDACTED] (assuming the [REDACTED] is not exercised), the interests or short positions of our Directors and chief executive in the shares, underlying shares and debentures of our Company or our associated corporations (within the meaning of Part XV of the SFO) which will have to be notified to our Company and the Stock Exchange pursuant to Divisions 7 and 8 of Part XV of the SFO (including interests or short positions which they are taken or deemed to have under such provisions of the SFO) or which will be required, pursuant to section 352 of the SFO, to be entered in the register referred to therein, or which will be required, pursuant to the Model Code for Securities Transactions by Directors of Listed Issuers as set out in Appendix C3 to the Listing Rules, to be notified to our Company and the Stock Exchange, once the H Shares are [REDACTED], are set out below:

(i) Interest in our Company

Name of Director or chief executive	Nature of interest	Number and class of Shares held ^(Note 1)	Shareholding in the total issued share capital upon completion of the [REDACTED] ^(Note 2)
Mr. Long	Beneficial owner	[REDACTED]	[REDACTED]
	Interest in controlled corporation ^(Note 3 and 5)	[REDACTED]	[REDACTED]

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Name of Director or chief executive	Nature of interest	Number and class of Shares held ^(Note 1)	Shareholding in the total issued share capital upon completion of the [REDACTED] ^(Note 2)
	Interest held jointly with other persons ^(Note 4)	[REDACTED]	[REDACTED]
Mr. Wang	Beneficial owner	[REDACTED]	[REDACTED]
	Interest held jointly with other persons ^(Note 4)	[REDACTED]	[REDACTED]
Mr. Ai	Beneficial owner	[REDACTED]	[REDACTED]
	Interest held jointly with other persons ^(Note 4)	[REDACTED]	[REDACTED]

Notes:

- (1) All interests stated are long positions.
- (2) The calculation is based on the total number of [REDACTED] Shares in issue immediately following the completion of the [REDACTED] (assuming the [REDACTED] is not exercised).
- (3) Mr. Long is the general partner of Longxin Tianxia I, Longxin Tianxia II, Longxin Tianxia III and Longxin Tianxia IV. By virtue of the SFO, Mr. Long is deemed to be interested in the Shares held by Longxin Tianxia I, Longxin Tianxia II, Longxin Tianxia III and Longxin Tianxia IV.
- (4) Mr. Long, Mr. Wang and Mr. Ai have entered into the Concert Party Agreement. By virtue of the SFO, each of Mr. Long, Mr. Wang and Mr. Ai are deemed to be interested in the Shares held by each other. For details of the Concert Party Agreement, please refer to the section headed “Relationship with our Controlling Shareholders” in this document.
- (5) As of the Latest Practicable Date, the general partner of Shenzhen Xingangtong was Huo Yue Zai Yuan, which was owned as to 99.0% by Mr. Long. By virtue of the SFO, Mr. Long is deemed to be interested in the Shares held by Shenzhen Xingangtong.

(ii) Interest in our associated corporations

Save as disclosed in this document, so far as our Directors are aware, immediately following the completion of the [REDACTED], no Directors or the chief executive will, directly or indirectly, be interested in the shares or underlying shares of the associated corporations of our Company.

(b) Interests of our Substantial Shareholders

Save as disclosed in “Substantial Shareholders” in this document, our Directors are not aware of any person (other than a Director or chief executive of our Company) who will have an interest or a short position in the shares or underlying shares of our Company which would fall to be disclosed to our Company under the provisions of Divisions 2 and 3 of Part XV of the SFO, or will be, directly or indirectly, interested in 10% or more of the issued voting shares of our Company.

2. Directors’ Service Contracts

We have entered into a service contract with each of our Directors. The principal particulars of these service contracts comprise (a) the term of the service; (b) termination provisions; and (c) dispute resolution provision. The service contracts may be renewed in accordance with our Articles of Association and the applicable laws, rules and regulations from time to time.

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Save as disclosed above, none of our Directors have entered, or have proposed to enter, a service contract with any member of our Group (other than contracts expiring or determinable by the employer within one year without the payment of compensation (other than statutory compensation)).

3. Directors’ Remuneration

For the years ended 31 December 2024 and 2025 and the three months ended 31 March 2026, the aggregate remuneration paid and benefits in kind granted to our Directors by our Group were approximately RMB3.3 million, RMB3.7 million and RMB1.1 million respectively. For details, please refer to Note 12 to the Accountants’ Report set out in Appendix I to this document.

Under the arrangements in force at the date of this document, we estimate the aggregate remuneration payable to, and benefits in kind receivable by, our Directors by our Group in respect of the year ending 31 December 2026 to be approximately RMB3.4 million.

D. OTHER INFORMATION

1. Estate Duty

Our Directors have been advised that no material liability for estate duty would be likely to fall upon any member of our Group.

2. Litigation

Save as disclosed in this document and so far as our Directors are aware, no litigation or claim of material importance is pending or threatened against any member of our Group.

3. Joint Sponsors

Each of the Joint Sponsors satisfies the criteria of independence applicable to sponsors set out in Rule 3A.07 of the Listing Rules.

The Joint Sponsors have made an application on our behalf to the Stock Exchange for a [REDACTED] of, and permission to deal in, the H Shares in issue and to be issued pursuant to the [REDACTED] (including any additional H Shares which may be issued pursuant to the exercise of the [REDACTED]). Our Company has agreed to pay the Joint Sponsors a total fee of USD640,000 to act as a sponsor in connection with the [REDACTED].

4. No Material Adverse Change

Save as disclosed in this document, our Directors confirm that there has been no material adverse change in the financial or trading position of our Group since 31 March 2026, being the end of the period reported on in the Accountants’ Report set out in Appendix I to this document.

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5. Qualification and Consent of Experts

This document contains statements made by the following experts:

Name	Qualification
GF Capital (Hong Kong) Limited	A licensed corporation to conduct Type 6 (advising on corporate finance) regulated activity under the SFO
CITIC Securities (Hong Kong) Limited	A licensed corporation to conduct Type 4 (advising on securities) and Type 6 (advising on corporate finance) regulated activity under the SFO
JunZeJun Law Offices	Legal advisers to our Company as to PRC Laws
Deloitte Touche Tohmatsu	Certified Public Accountants and Registered Public Interest Entity Auditor
China Insights Consultancy	Industry consultant

As of the Latest Practicable Date, none of the experts named above had any shareholding in any member of our Group or the right (whether legally enforceable or not) to subscribe for or to nominate persons to subscribe for securities in any member of our Group.

The experts named above have each given and have not withdrawn their respective written consents to the issue of this document with copies of their reports, letters, opinions or summaries of opinions (as the case maybe) and references to their names included in the form and context in which they are respectively included.

6. Promoter

The promoters of our Company are Mr. Long, Longxin Tianxia I, Ningbo HongShan Zhisheng, Shanghai Guotou, Ms. Shen Yue, Shenzhen Hongtu Xinghe, Mr. Wang Bin, Shenzhen Capital Group, Mr. Ai, Longxin Tianxia II, Longxin Tianxia III, Shenzhen Luohu Hongtu, Longxin Tianxia IV, Jiaying Danen, Shaoguan Zhongtoubang. For details of the promoters of our Company, please refer to the section headed “History, Development and Corporate Structure” in this document.

Save for the [REDACTED] and as disclosed in this document, within the two years immediately preceding the date of this document, no cash, securities, amount or other benefit has been paid, allotted or given or given, or has been proposed to be paid, allotted or given, to any of the promoters named above in connection with the [REDACTED] or the related transactions described in this document.

7. Preliminary Expenses

We have not incurred any material preliminary expenses.

8. Binding Effect

This document shall have the effect, where an application is made in pursuance hereof, of rendering all persons concerned bound by all of the provisions (other than the penal provisions) of sections 44A and 44B of the CWUMPO insofar as applicable.

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9. Bilingual Document

The English language and Chinese language versions of this document are being published separately in reliance upon the exemption provided by section 4 of the Companies (Exemption of Companies and Prospectuses from Compliance with Provisions) Notice (Chapter 32L of the Laws of Hong Kong).

10. Miscellaneous

- (a) Save as disclosed in this document, within the two years immediately preceding the date of this document:
 - (i) no commissions, discounts, brokerages or other special terms have been granted in connection with the issue or sale of any capital of any member of our Group, and no Directors, promoters or experts named in “— E. Other Information — 5. Qualification and Consent of Experts” in this section have received any such payment or benefit;
 - (ii) no capital of any member of our Group has been issued or is proposed to be issued for cash or issued as fully or partly paid up otherwise than in cash;
 - (iii) none of our Directors or the experts named in “— E. Other Information — 5. Qualification and Consent of Experts” in this section have any interest, direct or indirect, in the promotion of, or in any assets which have been, acquired or disposed of by or leased to, any member of our Group, or are proposed to be acquired or disposed of by or leased to any member of our Group; and
 - (iv) no commissions (but not including commissions to sub-[REDACTED]) have been paid or payable for subscribing or agreeing to subscribe, or procuring or agreeing to procure subscriptions, for any Shares or debentures of our Company.
- (b) Save as disclosed in this document:
 - (i) there is no arrangement under which future dividends are waived or agreed to be waived;
 - (ii) our Company has no outstanding convertible debt securities or debentures;
 - (iii) there are no founder, management or deferred shares in our Company or any of our subsidiaries;
 - (iv) no capital of any member of our Group is under option, or is agreed conditionally or unconditionally to be put under option;
 - (v) there has not been any interruption in the business of our Group which may have or have had a significant effect on our financial position in the 12 months immediately preceding the date of this document; and
 - (vi) none of our Directors are materially interested in any contract or arrangement subsisting at the date of this document which is significant in relation to the business of our Group.